

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
50V	1.6Ω @ $V_{GS} = 10V$	360mA
	2.5Ω @ $V_{GS} = 4.5V$	250mA

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

Features

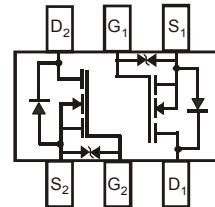
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD protected to 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208^(e3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)



Top View

Top View
Internal Schematic

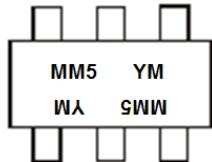
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN53D0LDW-7	SOT363	3000/Tape & Reel
DMN53D0LDW-13	SOT363	10000/Tape & Reel

Notes:

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



MM5 = Product Type Marking Code

YM = Date Code Marking

Y = Year (ex: B = 2014)

M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020					
Code	B	C	D	E	F	G	H					
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current (Note 5)	I_D	360	mA

 Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	R_{JJA}	411	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

 Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	—	—	V	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 50\text{V}$, $V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}	—	—	10	μA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(\text{th})}$	0.8	—	1.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	—	1.6	Ω	$V_{GS} = 10\text{V}$, $I_D = 500\text{mA}$
		—	—	2.5		$V_{GS} = 4.5\text{V}$, $I_D = 200\text{mA}$
		—	—	4.5		$V_{GS} = 2.5\text{V}$, $I_D = 100\text{mA}$
Source-Drain Diode Forward Voltage	V_{SD}	—	—	1.4	V	$V_{GS} = 0\text{V}$, $I_S = 500\text{mA}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	46	—	pF	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	5.3	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	4.0	—	pF	$V_{GS} = 4.5\text{V}$, $V_{DS} = 10\text{V}$, $I_D = 250\text{mA}$
Total Gate Charge	Q_g	—	0.6	—	nC	
Gate-Source Charge	Q_{gs}	—	0.2	—	nC	$V_{DD} = 30\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\Omega$, $I_D = 200\text{mA}$
Gate-Drain Charge	Q_{gd}	—	0.1	—	nC	
Turn-On Delay Time	$t_{D(\text{on})}$	—	2.7	—	ns	$V_{DD} = 30\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\Omega$, $I_D = 200\text{mA}$
Turn-On Rise Time	t_r	—	2.5	—	ns	
Turn-Off Delay Time	$t_{D(\text{off})}$	—	19	—	ns	
Turn-Off Fall Time	t_f	—	11	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Short duration pulse test used to minimize self-heating effect.

7. Guaranteed by design. Not subject to product testing.

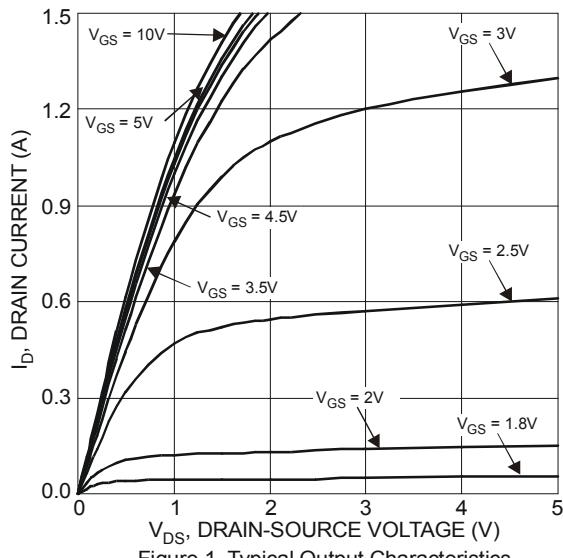


Figure 1 Typical Output Characteristics

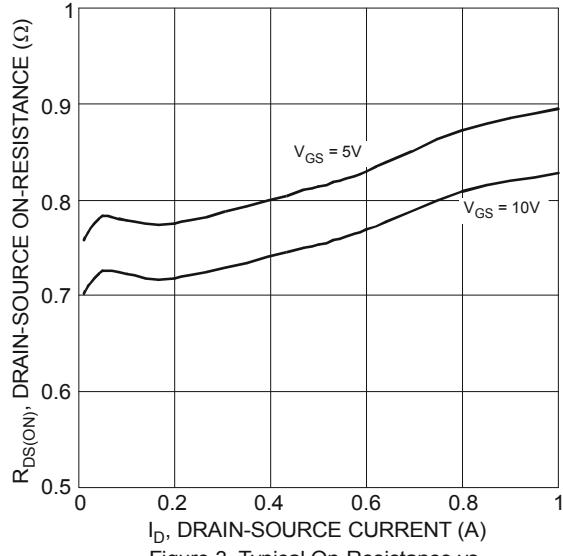


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

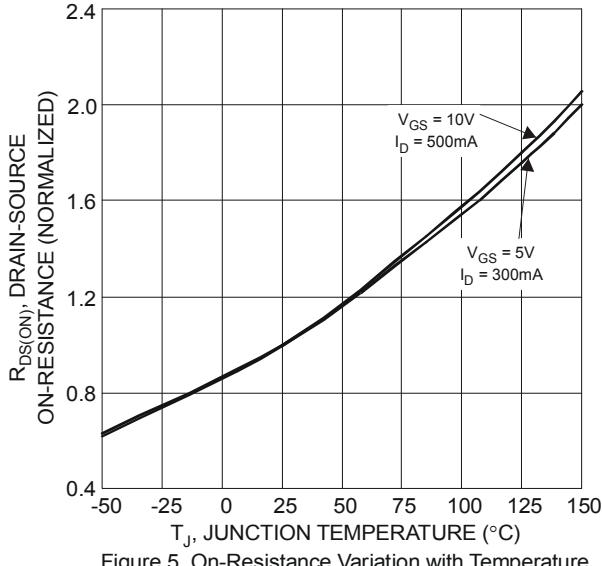


Figure 5 On-Resistance Variation with Temperature

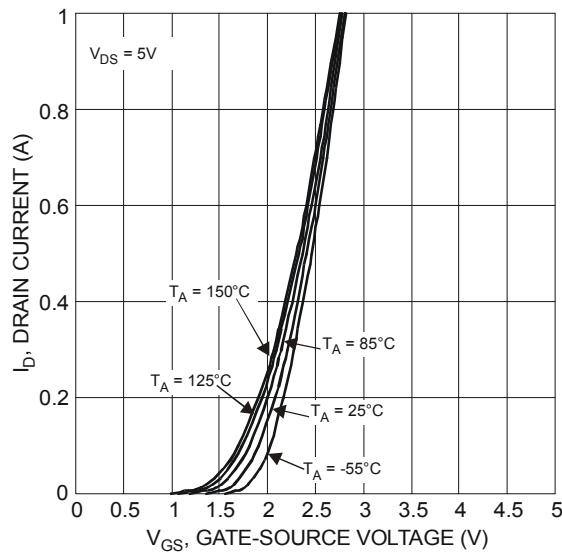


Figure 2 Typical Transfer Characteristics

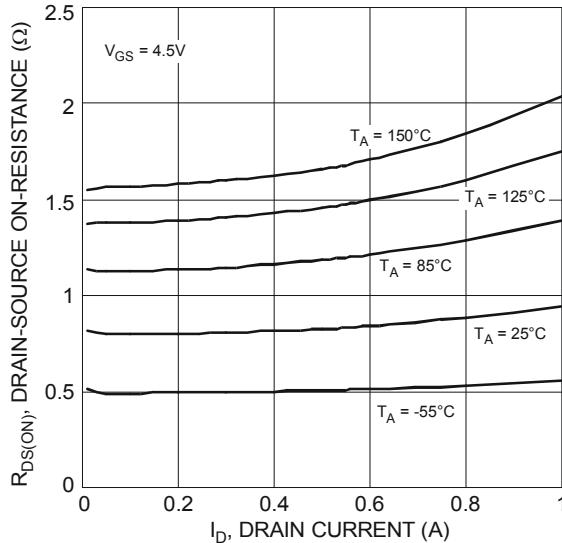


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

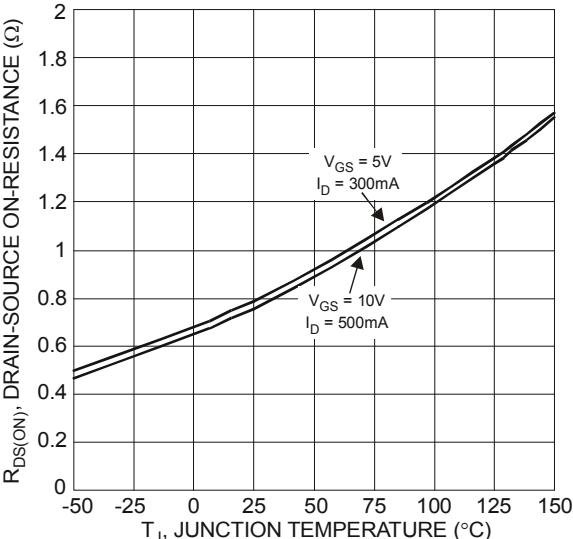


Figure 6 On-Resistance Variation with Temperature

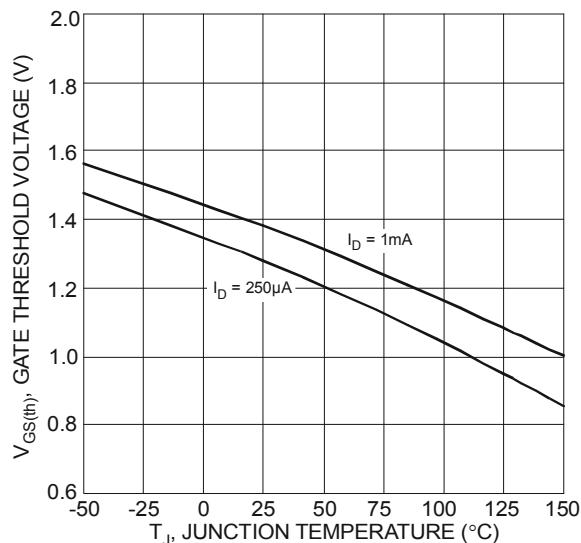


Figure 7 Gate Threshold Variation vs. Ambient Temperature

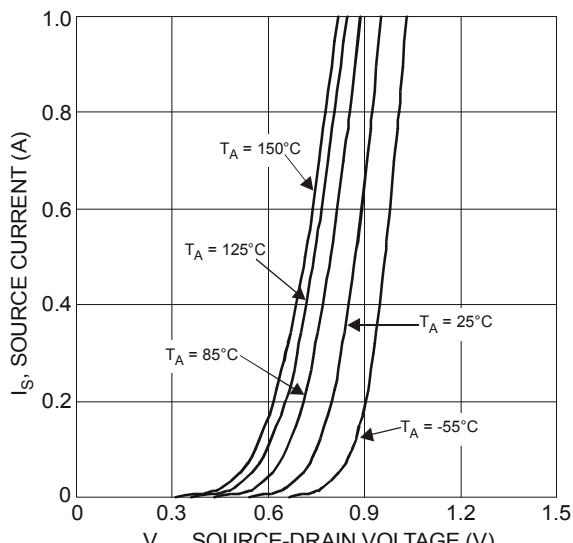


Figure 8 Diode Forward Voltage vs. Current

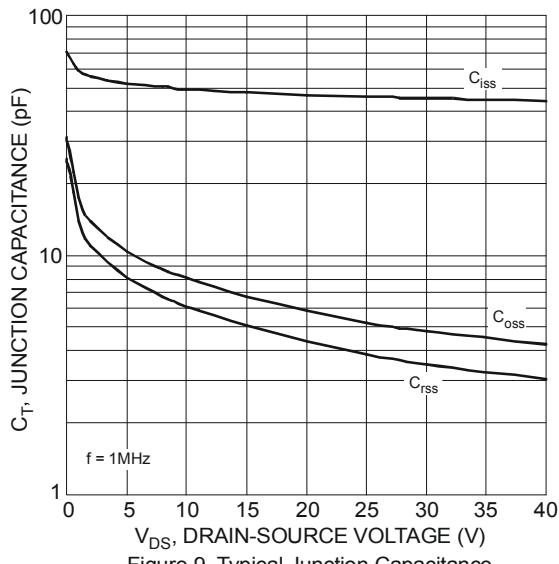


Figure 9 Typical Junction Capacitance

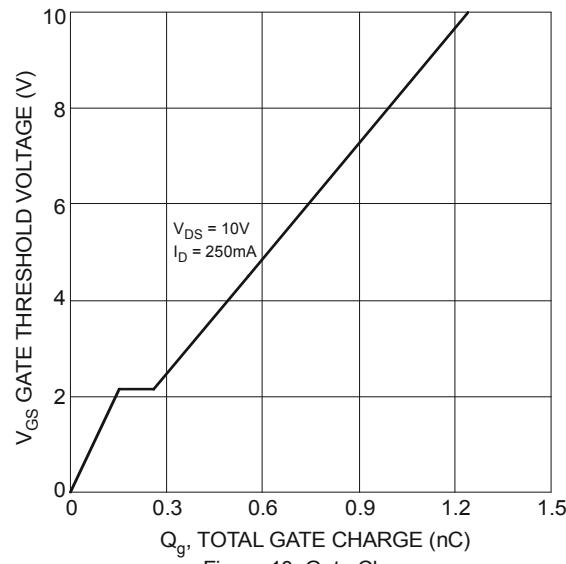
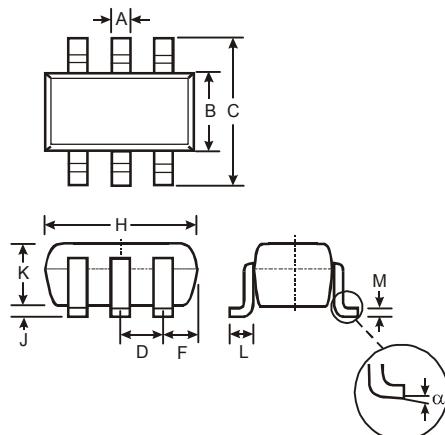


Figure 10 Gate Charge

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.

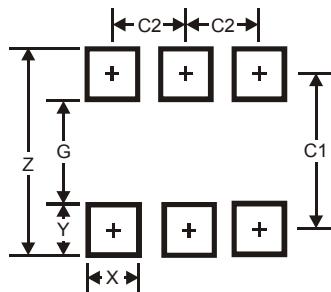


SOT363			
Dim	Min	Max	Typ
A	0.10	0.30	0.25
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.65 Typ		
F	0.40	0.45	0.425
H	1.80	2.20	2.15
J	0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.22	0.11
α	0°	8°	-

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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